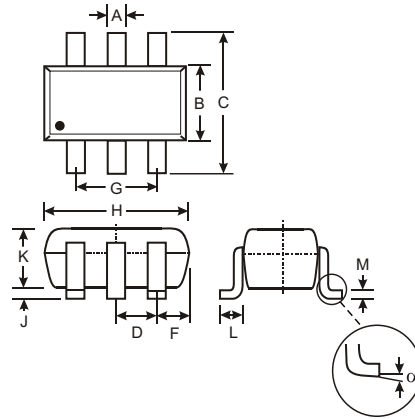


Features

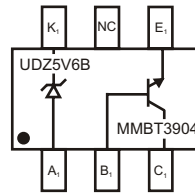
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Lead Free Product

Mechanical Data

- Case: SOT-363, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram Below
- Marking: A96
- Date Code & Marking Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		



Maximum Ratings, Total Device @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Maximum Ratings, NPN Transistor Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	200	mA

Maximum Ratings, Zener Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ $I_F = 10\text{mA}$	V_F	0.9	V

Notes: 1. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics, NPN Transistor Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Base Cutoff Current	I_{BL}	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	40 70 100 60 30	— — 300 — —	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.65 —	0.85 0.95	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.0	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	8.0	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1.0	10	k Ω	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.5	8.0	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	$V_{CE} = 20\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	5.0	dB	$V_{CE} = 5.0\text{V}, I_C = 100\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA}, V_{BE(off)} = -0.5\text{V}, I_{B1} = 1.0\text{mA}$
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	200	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA}, I_{B1} = I_{B2} = 1.0\text{mA}$
Fall Time	t_f	—	50	ns	

Electrical Characteristics, Zener Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Type Number	Zener Voltage Range (Note 2)				Maximum Zener Impedance		Maximum Reverse Leakage Current	
	$V_Z @ I_{ZT}$			I_{ZT}	$Z_{ZT} @ I_{ZT}$	$Z_{ZK} @ I_{ZK} = 0.5\text{mA}$	I_R	@ V_R
	Nom (V)	Min (V)	Max (V)	mA	Ω		μA	V
UDZ5V6B	5.6	5.49	5.73	5	60	200	1.0	2.5

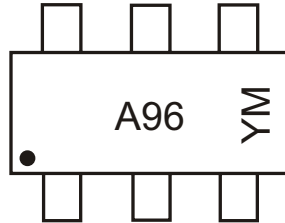
Notes: 2. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 3)

Device	Packaging	Shipping
ASMCC0096-7	SOT-363	3000/Tape & Reel
ASMCC0096-13	SOT-363	10,000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

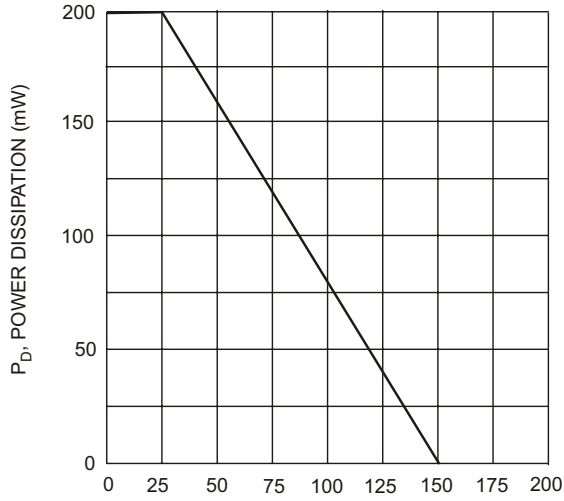


A96 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

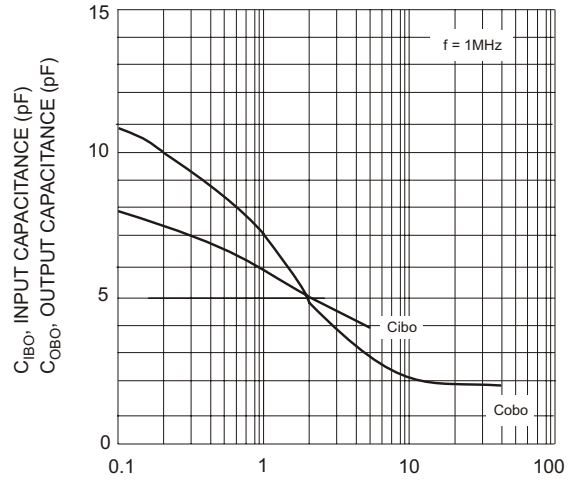
Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

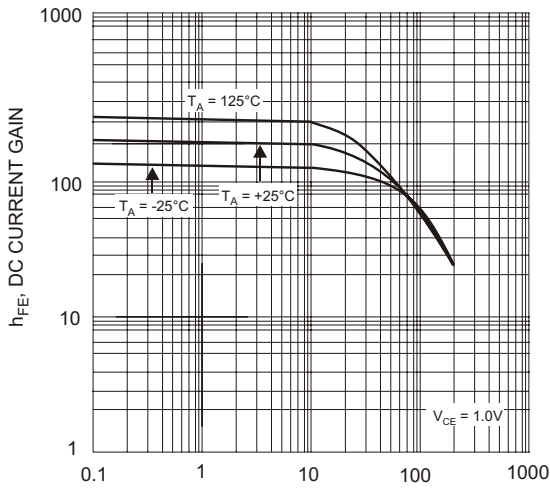
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



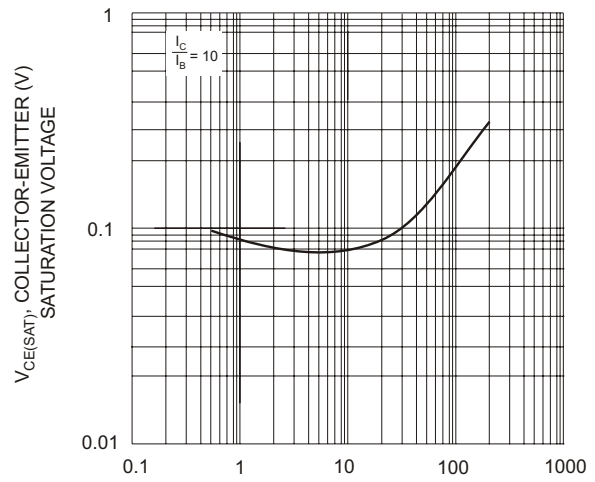
T_A, AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs Ambient Temperature (Total Device)



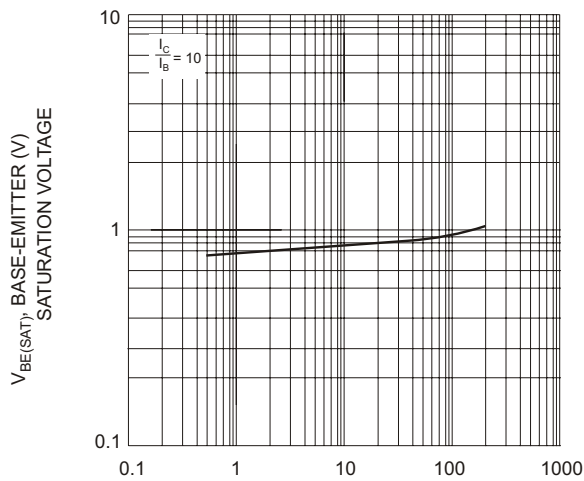
V_{CB}, COLLECTOR-BASE VOLTAGE (V)
Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage (Transistor Element)



I_C, COLLECTOR CURRENT (mA)
Fig. 3, Typical DC Current Gain vs Collector Current (Transistor Element)



I_C, COLLECTOR CURRENT (mA)
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current (Transistor Element)



I_C, COLLECTOR CURRENT (mA)
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current (Transistor Element)

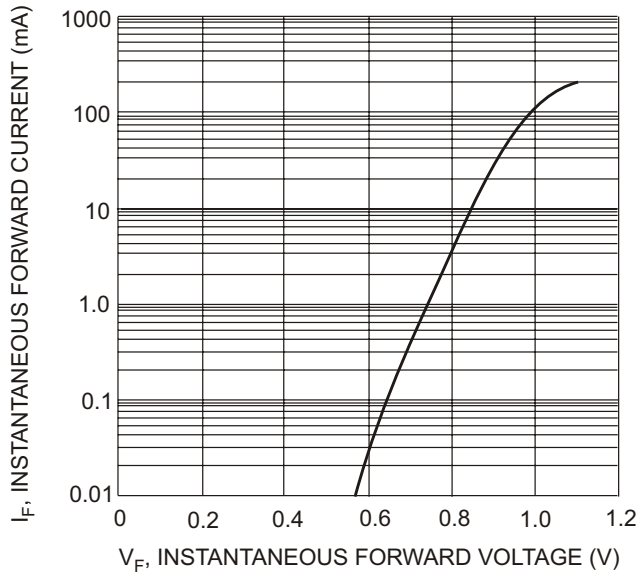


Fig. 6 Typical Forward Characteristics